

<b>Notice of References Cited</b>		Application/Control No.	Applicant(s)/Patent Under Reexamination INOUE ET AL.	
		Examiner Belur V Keshavan	Art Unit 2825	Page 1 of 1

**U.S. PATENT DOCUMENTS**

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	C	US-6,548,333	04-2003	Smith, Richard Peter	438/172
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	M	US-			

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**NON-PATENT DOCUMENTS**

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	V	Sullivan et al., High-Power 10 GHz operation of AlGaN HFETs on insulating SiC, IEEE Elect. Device Letters, Vol. 19, No 6, 1998
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.